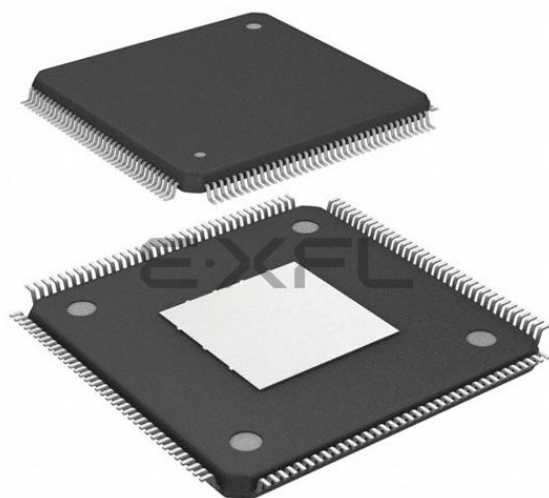




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Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	120MHz
Connectivity	CANbus, EBI/EMI, Ethernet, I ² C, LINbus, SPI, UART, USB
Peripherals	DMA, I ² S, LED, POR, PWM, WDT
Number of I/O	91
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	160K x 8
Voltage - Supply (Vcc/Vdd)	3.13V ~ 3.63V
Data Converters	A/D 32x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LQFP Exposed Pad
Supplier Device Package	PG-LQFP-144-13
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/xmc4500f144f1024acxqma1

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Summary of Features
Table 2 Features of XMC4500 Device Types (cont'd)

Derivative ¹⁾	LEDTS Intf.	SDMMC Intf.	EBU Intf. ²⁾	ETH Intf. ³⁾	USB Intf.	USIC Chan.	MultiCAN Nodes, MO
XMC4504-F144x512	1	1	SDM	-	-	3 x 2	-
XMC4504-F100x512	1	1	M16	-	-	3 x 2	-

1) x is a placeholder for the supported temperature range.

2) Memory types supported S=SDRAM, D=DEMUX, M=MUX 16-bit and 32-bit, M16=MUX 16-bit

3) Supported interfaces, M=MII, R=RMI.

Table 3 Features of XMC4500 Device Types

Derivative ¹⁾	ADC Chan.	DSD Chan.	DAC Chan.	CCU4 Slice	CCU8 Slice	POSIF Intf.
XMC4500-E144x1024	32	4	2	4 x 4	2 x 4	2
XMC4500-F144x1024	32	4	2	4 x 4	2 x 4	2
XMC4500-F100x1024	24	4	2	4 x 4	2 x 4	2
XMC4500-F144x768	32	4	2	4 x 4	2 x 4	2
XMC4500-F100x768	24	4	2	4 x 4	2 x 4	2
XMC4502-F100x768	24	4	2	4 x 4	2 x 4	2
XMC4504-F144x512	32	4	2	4 x 4	2 x 4	2
XMC4504-F100x512	24	4	2	4 x 4	2 x 4	2

1) x is a placeholder for the supported temperature range.

1.4 Definition of Feature Variants

The XMC4500 types are offered with several memory sizes and number of available VADC channels. [Table 4](#) describes the location of the available Flash memory, [Table 5](#) describes the location of the available SRAMs, [Table 6](#) the available VADC channels.

Table 4 Flash Memory Ranges

Total Flash Size	Cached Range	Uncached Range
512 Kbytes	0800 0000 _H – 0807 FFFF _H	0C00 0000 _H – 0C07 FFFF _H

Summary of Features
Table 4 Flash Memory Ranges (cont'd)

Total Flash Size	Cached Range	Uncached Range
768 Kbytes	0800 0000 _H – 080B FFFF _H	0C00 0000 _H – 0C0B FFFF _H
1,024 Kbytes	0800 0000 _H – 080F FFFF _H	0C00 0000 _H – 0C0F FFFF _H

Table 5 SRAM Memory Ranges

Total SRAM Size	Program SRAM	System Data SRAM	Communication Data SRAM
128 Kbytes	1000 0000 _H – 1000 FFFF _H	2000 0000 _H – 2000 FFFF _H	–
160 Kbytes	1000 0000 _H – 1000 FFFF _H	2000 0000 _H – 2000 FFFF _H	3000 0000 _H – 3000 7FFF _H

Table 6 ADC Channels¹⁾

Package	VADC G0	VADC G1	VADC G2	VADC G3
PG-LQFP-144 PG-LFBGA-144	CH0..CH7	CH0..CH7	CH0..CH7	CH0..CH7
PG-LQFP-100	CH0..CH7	CH0..CH7	CH0..CH3	CH0..CH3

1) Some pins in a package may be connected to more than one channel. For the detailed mapping see the Port I/O Function table.

1.5 Identification Registers

The identification registers allow software to identify the marking.

Table 7 XMC4500 Identification Registers

Register Name	Value	Marking
SCU_IDCHIP	0004 5002 _H	EES-AA, ES-AA
SCU_IDCHIP	0004 5003 _H	ES-AB, AB
SCU_IDCHIP	0004 5004 _H	AC
JTAG IDCODE	101D B083 _H	EES-AA, ES-AA
JTAG IDCODE	101D B083 _H	ES-AB, AB
JTAG IDCODE	401D B083 _H	AC

General Device Information
Table 9 Package Pin Mapping (cont'd)

Function	LQFP-144	LFBGA-144	LQFP-100	Pad Type	Notes
P0.11	139	E5	95	A1+	
P0.12	138	D5	94	A1+	
P0.13	137	C5	-	A1+	
P0.14	136	E6	-	A1+	
P0.15	135	C6	-	A1+	
P1.0	112	D9	79	A1+	
P1.1	111	E9	78	A1+	
P1.2	110	C11	77	A2	
P1.3	109	C12	76	A2	
P1.4	108	C10	75	A1+	
P1.5	107	D10	74	A1+	
P1.6	116	B9	83	A2	
P1.7	115	B10	82	A2	
P1.8	114	A10	81	A2	
P1.9	113	B11	80	A2	
P1.10	106	D12	73	A1+	
P1.11	105	D11	72	A1+	
P1.12	104	E11	71	A2	
P1.13	103	E12	70	A2	
P1.14	102	E10	69	A2	
P1.15	94	G12	68	A2	
P2.0	74	J11	52	A2	
P2.1	73	K12	51	A2	After a system reset, via HWSEL this pin selects the DB.TDO function.
P2.2	72	K11	50	A2	
P2.3	71	L11	49	A2	
P2.4	70	L10	48	A2	
P2.5	69	M10	47	A2	
P2.6	76	J9	54	A1+	
P2.7	75	K9	53	A1+	
P2.8	68	L9	46	A2	
P2.9	67	M9	45	A2	

3.1.4 Pad Driver and Pad Classes Summary

This section gives an overview on the different pad driver classes and their basic characteristics.

Table 17 Pad Driver and Pad Classes Overview

Class	Power Supply	Type	Sub-Class	Speed Grade	Load	Termination
A	3.3 V	LVTTTL I/O	A1 (e.g. GPIO)	6 MHz	100 pF	No
			A1+ (e.g. serial I/Os)	25 MHz	50 pF	Series termination recommended
			A2 (e.g. ext. Bus)	80 MHz	15 pF	Series termination recommended

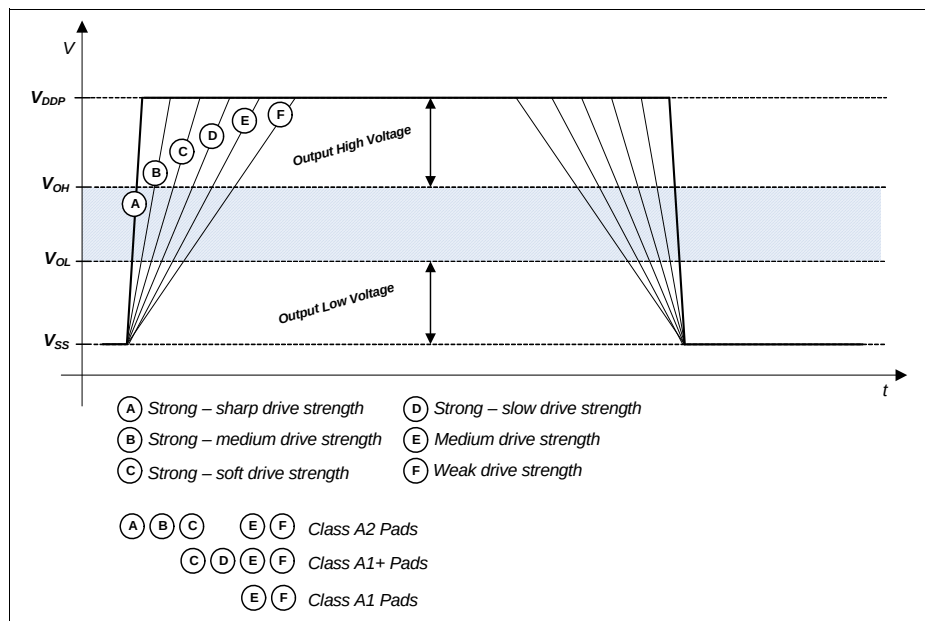


Figure 12 Output Slopes with different Pad Driver Modes

Figure 12 is a qualitative display of the resulting output slope performance with different output driver modes. The detailed input and output characteristics are listed in [Section 3.2.1](#).

3.1.5 Operating Conditions

The following operating conditions must not be exceeded in order to ensure correct operation and reliability of the XMC4500. All parameters specified in the following sections refer to these operating conditions, unless noted otherwise.

Table 18 Operating Conditions Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Ambient Temperature	T_A SR	-40	—	85	°C	Temp. Range F
		-40	—	105	°C	Temp. Range X
		-40	—	125	°C	Temp. Range K
Digital supply voltage	V_{DDP} SR	3.13 ¹⁾	3.3	3.63 ²⁾	V	
Core Supply Voltage	V_{DDC} CC	— ¹⁾	1.3	—	V	Generated internally
Digital ground voltage	V_{SS} SR	0	—	—	V	
Analog supply voltage	V_{DDA} SR	3.0	3.3	3.6 ²⁾	V	
Analog ground voltage for V_{DDA}	V_{SSA} SR	-0.1	0	0.1	V	
Battery Supply Voltage for Hibernate Domain	V_{BAT} SR	1.95 ³⁾	—	3.63	V	When V_{DDP} is supplied V_{BAT} has to be supplied as well.
System Frequency	f_{SYS} SR	—	—	120	MHz	
Short circuit current of digital outputs	I_{SC} SR	-5	—	5	mA	
Absolute sum of short circuit currents per pin group ⁴⁾	ΣI_{SC_PG} SR	—	—	20	mA	
Absolute sum of short circuit currents of the device	ΣI_{SC_D} SR	—	—	100	mA	

1) See also the Supply Monitoring thresholds, [Section 3.3.2](#).

2) Voltage overshoot to 4.0 V is permissible at Power-Up and $\overline{PORST}$ low, provided the pulse duration is less than 100 μ s and the cumulated sum of the pulses does not exceed 1 h over lifetime.

3) To start the hibernate domain it is required that $V_{BAT} \geq 2.1$ V, for a reliable start of the oscillation of RTC_XTAL in crystal mode it is required that $V_{BAT} \geq 3.0$ V.

4) The port groups are defined in [Table 16](#).

Table 22 Standard Pads Class_A2

Parameter	Symbol	Values		Unit	Note / Test Condition
		Min.	Max.		
Input Leakage current	I_{OZA2} CC	-6	6	μA	$0\text{ V} \leq V_{\text{IN}} < 0.5 \cdot V_{\text{DDP}} - 1\text{ V};$ $0.5 \cdot V_{\text{DDP}} + 1\text{ V} < V_{\text{IN}} \leq V_{\text{DDP}}$
		-3	3	μA	$0.5 \cdot V_{\text{DDP}} - 1\text{ V} < V_{\text{IN}} < 0.5 \cdot V_{\text{DDP}} + 1\text{ V}$
Input high voltage	V_{IHA2} SR	$0.6 \times V_{\text{DDP}}$	$V_{\text{DDP}} + 0.3$	V	max. 3.6 V
Input low voltage	V_{ILA2} SR	-0.3	$0.36 \times V_{\text{DDP}}$	V	
Output high voltage, POD = weak	V_{OHA2} CC	$V_{\text{DDP}} - 0.4$	–	V	$I_{\text{OH}} \geq -400\text{ }\mu\text{A}$
		2.4	–	V	$I_{\text{OH}} \geq -500\text{ }\mu\text{A}$
Output high voltage, POD = medium		$V_{\text{DDP}} - 0.4$	–	V	$I_{\text{OH}} \geq -1.4\text{ mA}$
		2.4	–	V	$I_{\text{OH}} \geq -2\text{ mA}$
Output high voltage, POD = strong		$V_{\text{DDP}} - 0.4$	–	V	$I_{\text{OH}} \geq -1.4\text{ mA}$
		2.4	–	V	$I_{\text{OH}} \geq -2\text{ mA}$
Output low voltage, POD = weak	V_{OLA2} CC	–	0.4	V	$I_{\text{OL}} \leq 500\text{ }\mu\text{A}$
Output low voltage, POD = medium		–	0.4	V	$I_{\text{OL}} \leq 2\text{ mA}$
Output low voltage, POD = strong		–	0.4	V	$I_{\text{OL}} \leq 2\text{ mA}$

3.2.7 Oscillator Pins

Note: It is strongly recommended to measure the oscillation allowance (negative resistance) in the final target system (layout) to determine the optimal parameters for the oscillator operation. Please refer to the limits specified by the crystal or ceramic resonator supplier.

Note: These parameters are not subject to production test, but verified by design and/or characterization.

The oscillator pins can be operated with an external crystal (see [Figure 20](#)) or in direct input mode (see [Figure 21](#)).

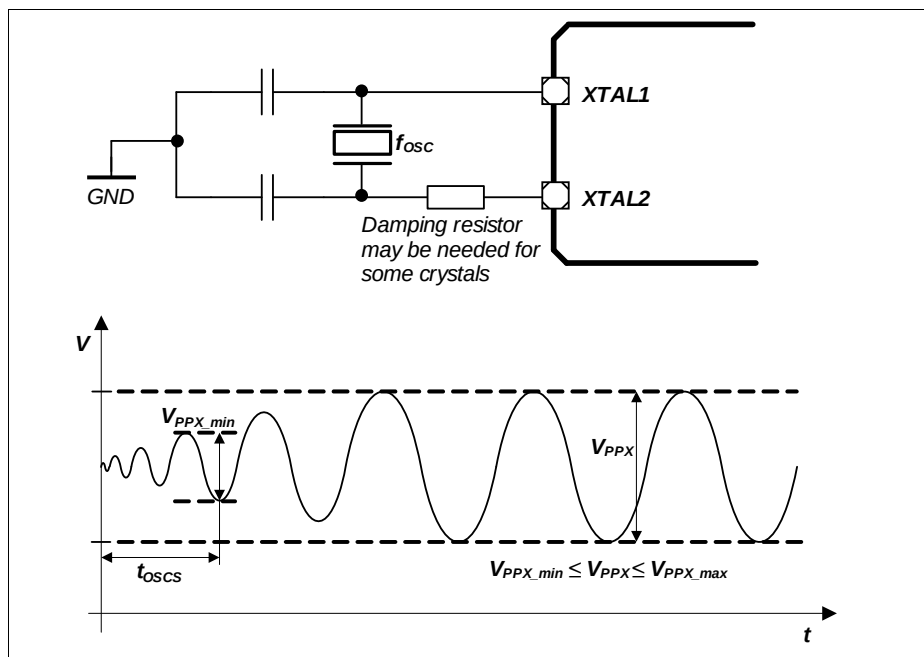


Figure 20 Oscillator in Crystal Mode

Table 35 Power Sequencing Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Positive Load Step Current	ΔI_{PLS} SR	-	-	50	mA	Load increase on V_{DDP} $\Delta t \leq 10$ ns
Negative Load Step Current	ΔI_{NLS} SR	-	-	150	mA	Load decrease on V_{DDP} $\Delta t \leq 10$ ns
V_{DDC} Voltage Over- / Undershoot from Load Step	ΔV_{LS} CC	-	-	± 100	mV	For maximum positive or negative load step
Positive Load Step Settling Time	t_{PLSS} SR	50	-	-	μ s	
Negative Load Step Settling Time	t_{NLSS} SR	100	-	-	μ s	
External Buffer Capacitor on V_{DDC}	C_{EXT} SR	-	10	-	μ F	In addition $C = 100$ nF capacitor on each V_{DDC} pin

Positive Load Step Examples

System assumptions:

$f_{CPU} = f_{SYS}$, target frequency $f_{CPU} = 120$ MHz, main PLL $f_{VCO} = 480$ MHz, stepping done by K2 divider, t_{PLSS} between individual steps:

24 MHz - 48 MHz - 68 MHz - 96 MHz - 120 MHz (K2 steps 20 - 10 - 7 - 5 - 4)

24 MHz - 68 MHz - 96 MHz - 120 MHz (K2 steps 20 - 7 - 5 - 4)

24 MHz - 68 MHz - 120 MHz (K2 steps 20 - 7 - 4)

3.3.4 Phase Locked Loop (PLL) Characteristics

Note: These parameters are not subject to production test, but verified by design and/or characterization.

Main and USB PLL

Table 36 PLL Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Accumulated Jitter	D_p CC	–	–	±5	ns	accumulated over 300 cycles $f_{SYS} = 120$ MHz
Duty Cycle ¹⁾	D_{DC} CC	46	50	54	%	Low pulse to total period, assuming an ideal input clock source
PLL base frequency	$f_{PLLBASE}$ CC	30	–	140	MHz	
VCO input frequency	f_{REF} CC	4	–	16	MHz	
VCO frequency range	f_{VCO} CC	260	–	520	MHz	
PLL lock-in time	t_L CC	–	–	400	µs	

1) 50% for even K2 divider values, 50±(10/K2) for odd K2 divider values.

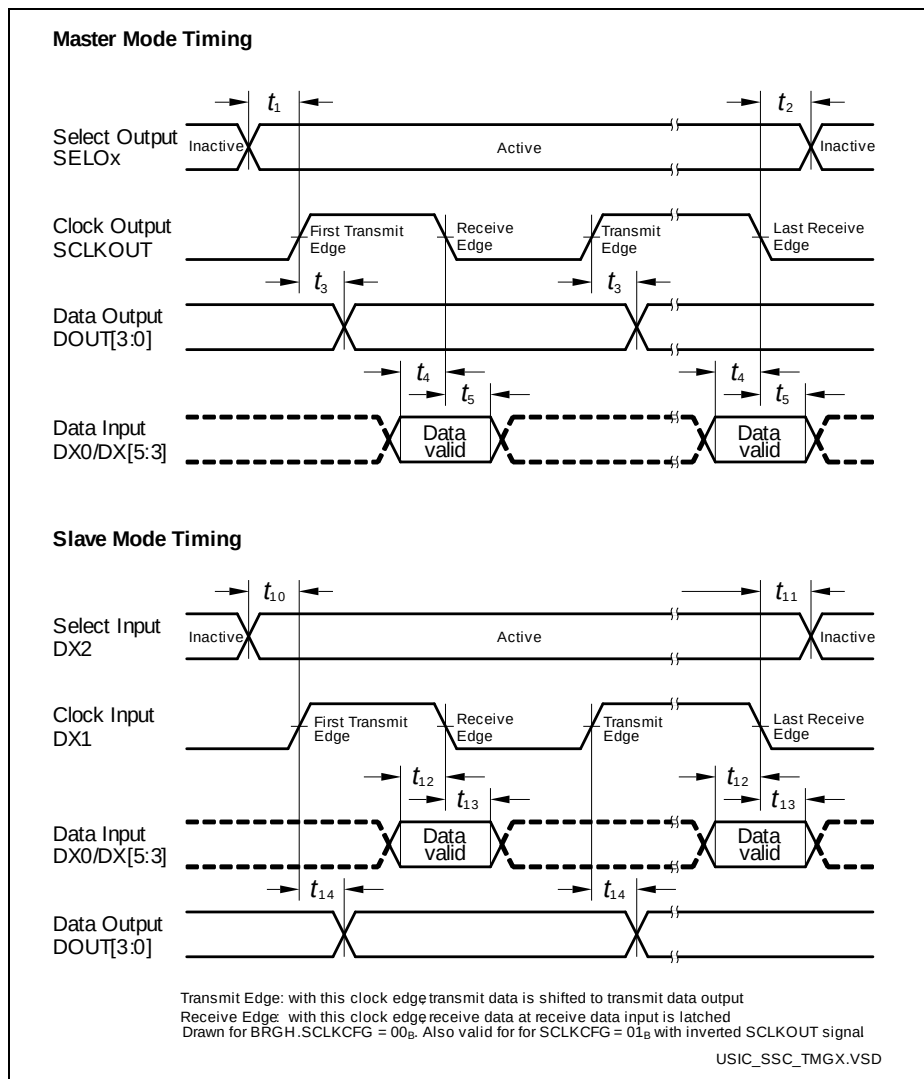


Figure 33 USIC - SSC Master/Slave Mode Timing

Note: This timing diagram shows a standard configuration, for which the slave select signal is low-active, and the serial clock signal is not shifted and not inverted.

Table 46 USIC IIC Fast Mode Timing¹⁾

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Fall time of both SDA and SCL	t_1 CC/SR	20 + $0.1 \cdot C_b$ ²⁾	-	300	ns	
Rise time of both SDA and SCL	t_2 CC/SR	20 + $0.1 \cdot C_b$ ²⁾	-	300	ns	
Data hold time	t_3 CC/SR	0	-	-	μs	
Data set-up time	t_4 CC/SR	100	-	-	ns	
LOW period of SCL clock	t_5 CC/SR	1.3	-	-	μs	
HIGH period of SCL clock	t_6 CC/SR	0.6	-	-	μs	
Hold time for (repeated) START condition	t_7 CC/SR	0.6	-	-	μs	
Set-up time for repeated START condition	t_8 CC/SR	0.6	-	-	μs	
Set-up time for STOP condition	t_9 CC/SR	0.6	-	-	μs	
Bus free time between a STOP and START condition	t_{10} CC/SR	1.3	-	-	μs	
Capacitive load for each bus line	C_b SR	-	-	400	pF	

1) Due to the wired-AND configuration of an IIC bus system, the port drivers of the SCL and SDA signal lines need to operate in open-drain mode. The high level on these lines must be held by an external pull-up device, approximately 10 kOhm for operation at 100 kbit/s, approximately 2 kOhm for operation at 400 kbit/s.

2) C_b refers to the total capacitance of one bus line in pF.

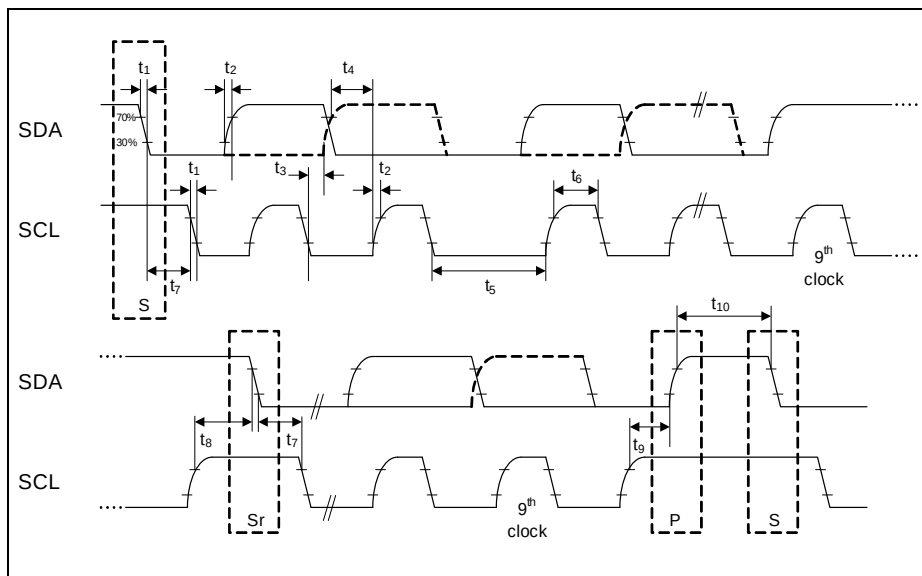


Figure 34 USIC IIC Stand and Fast Mode Timing

3.3.9.4 Inter-IC Sound (IIS) Interface Timing

The following parameters are applicable for a USIC channel operated in IIS mode.

Note: These parameters are not subject to production test, but verified by design and/or characterization.

Table 47 USIC IIS Master Transmitter Timing

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Clock period	t_1 CC	33.3	—	—	ns	
Clock high time	t_2 CC	$0.35 \times t_{1min}$	—	—	ns	
Clock low time	t_3 CC	$0.35 \times t_{1min}$	—	—	ns	
Hold time	t_4 CC	0	—	—	ns	
Clock rise time	t_5 CC	—	—	$0.15 \times t_{1min}$	ns	

Table 52 SD Card Bus Timing for High-Speed Mode¹⁾

Parameter	Symbol	Values		Unit	Note/ Test Condition
		Min.	Max.		
SD card input setup time	t_{ISU}	6	–	ns	
SD card input hold time	t_{IH}	2	–	ns	
SD card output valid time	t_{ODLY}	–	14	ns	
SD card output hold time	t_{OH}	2.5	–	ns	

1) Reference card timing values for calculation examples. Not subject to production test and not characterized.

High-Speed Output Path (Write)

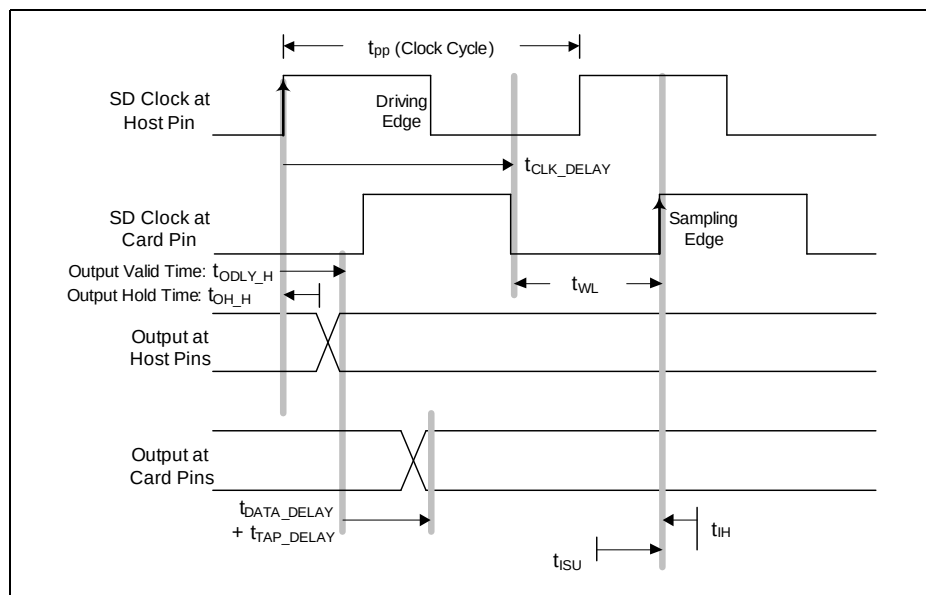


Figure 39 High-Speed Output Path

High-Speed Write Meeting Setup (Maximum Delay)

The following equations show how to calculate the allowed skew range between the SD_CLK and SD_DAT/CMD signals on the PCB.

Read Timing

Table 54 Asynchronous Read Timing, Multiplexed and Demultiplexed

Parameter			Symbol	Limit Values		Unit
				Min.	Max.	
A(24:16) output delay	to $\overline{\text{RD}}$ rising edge, deviation from the ideal programmed value.	CC	t_0	-2.5	2.5	ns
A(24:16) output delay		CC	t_1	-2.5	2.5	
$\overline{\text{CS}}$ rising edge		CC	t_2	-2	2.5	
$\overline{\text{ADV}}$ rising edge		CC	t_3	-1.5	4.5	
$\overline{\text{BC}}$ rising edge		CC	t_4	-2.5	2.5	
$\overline{\text{WAIT}}$ input setup		SR	t_5	12	—	
$\overline{\text{WAIT}}$ input hold		SR	t_6	0	—	
Data input setup		SR	t_7	12	—	
Data input hold		SR	t_8	0	—	
RD / $\overline{\text{WR}}$ output delay		CC	t_9	-2.5	1.5	

Multiplexed Read Timing

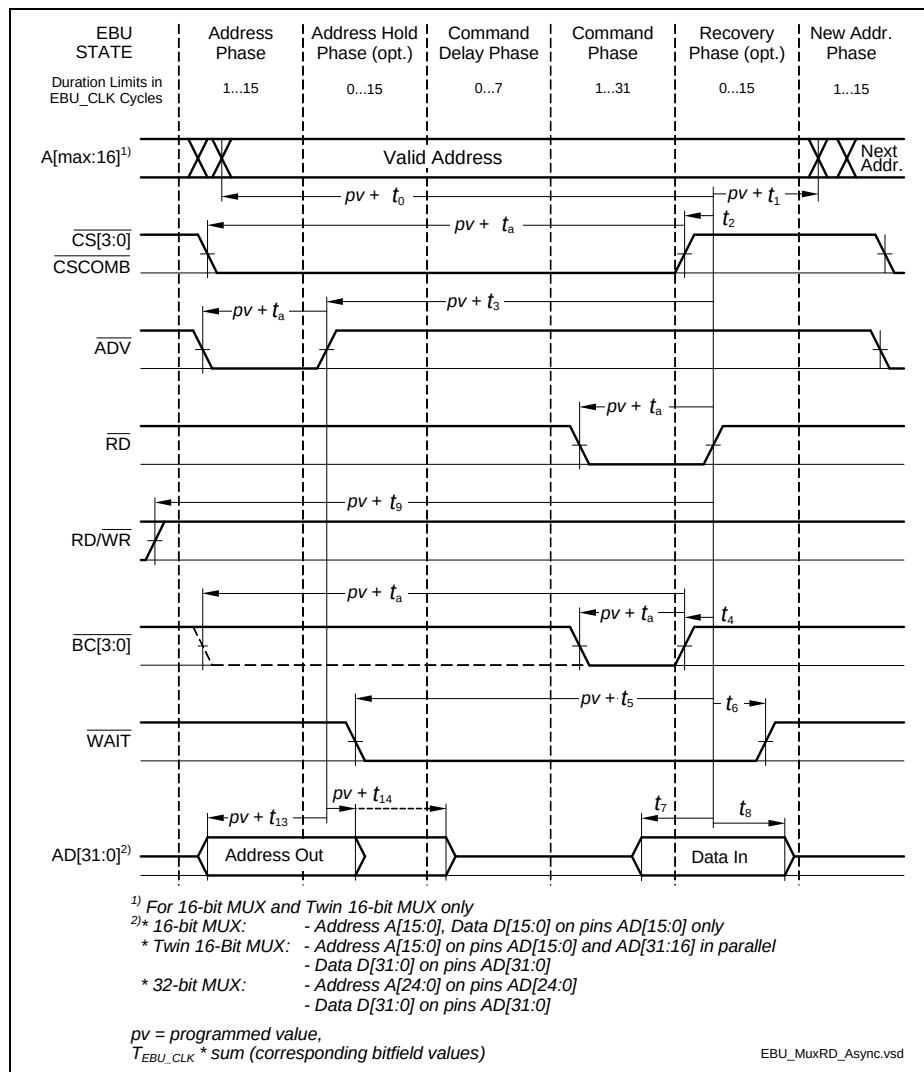


Figure 41 Multiplexed Read Access

Electrical Parameters

- 3) If the clock feedback is not enabled, the input signals are latched using the internal clock in the same way as for asynchronous access. Thus, t_5 , t_6 , t_7 and t_8 from the asynchronous timing apply.

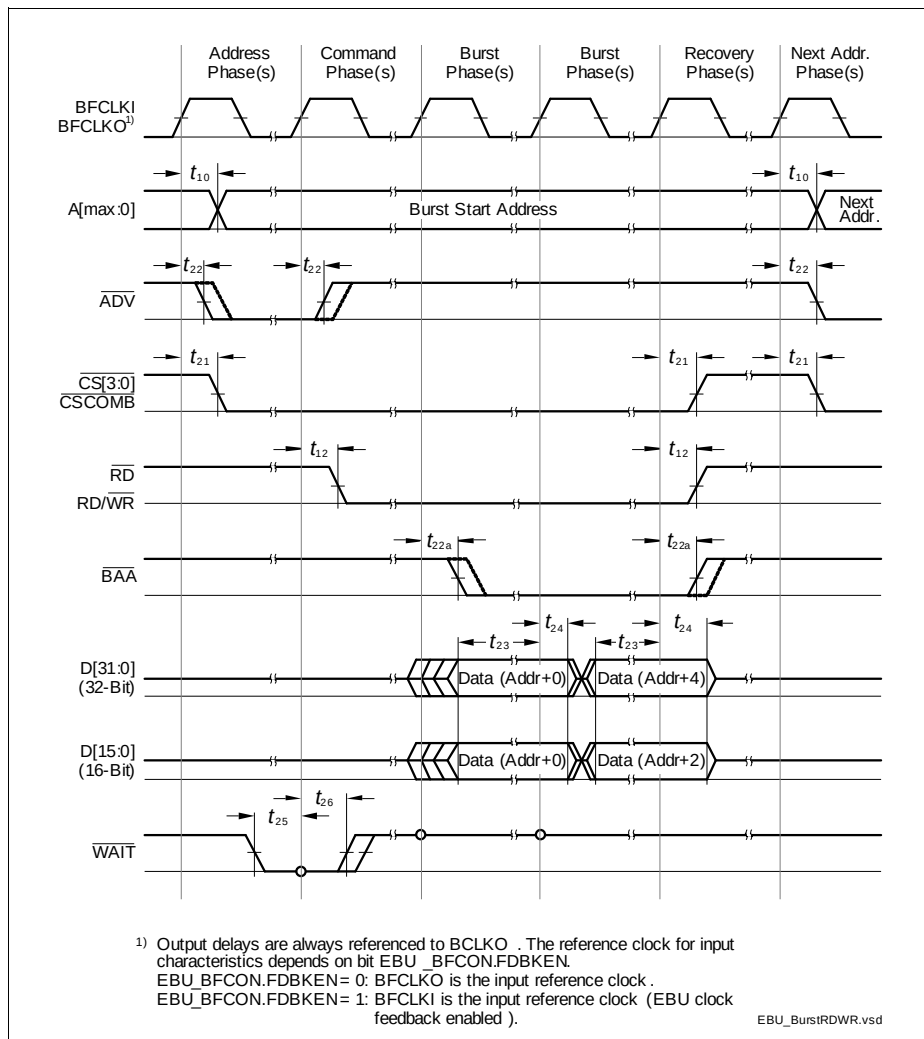


Figure 45 EBU Burst Mode Read / Write Access Timing

3.3.12.2 ETH Management Signal Parameters (ETH_MDC, ETH_MDIO)

Table 61 ETH Management Signal Timing Parameters

Parameter	Symbol		Values			Unit	Note / Test Condi on
			Min.	Typ.	Max.		
ETH_MDC period	t_1	CC	400	—	—	ns	$C_L = 25 \text{ pF}$
ETH_MDC high time	t_2	CC	160	—	—	ns	
ETH_MDC low time	t_3	CC	160	—	—	ns	
ETH_MDIO setup time (output)	t_4	CC	10	—	—	ns	
ETH_MDIO hold time (output)	t_5	CC	10	—	—	ns	
ETH_MDIO data valid (input)	t_6	SR	0	—	300	ns	

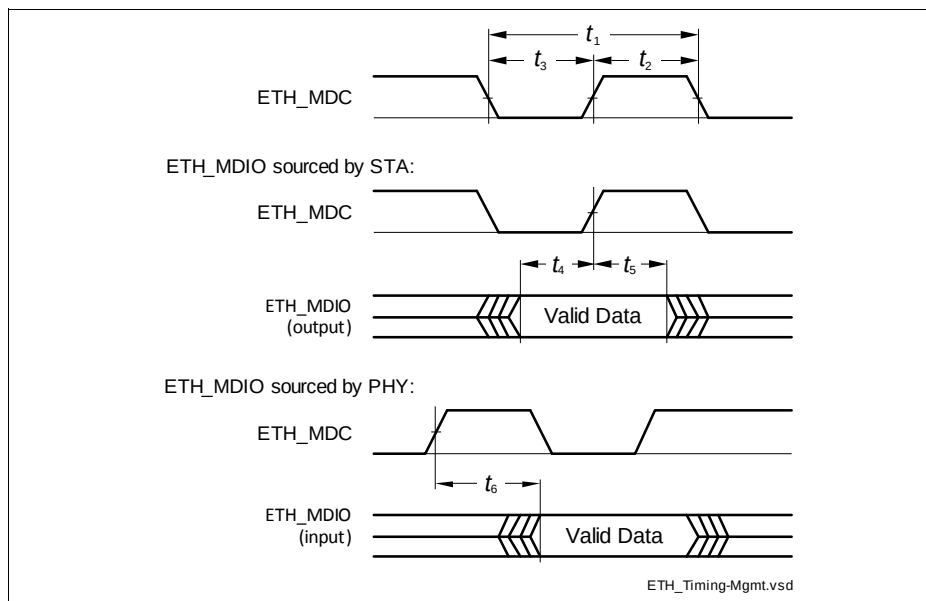


Figure 52 ETH Management Signal Timing

3.3.12.3 ETH MII Parameters

In the following, the parameters of the MII (Media Independent Interface) are described.

Table 62 ETH MII Signal Timing Parameters

Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
Clock period, 10 Mbps	t_7	SR	400	–	–	ns	$C_L = 25 \text{ pF}$
Clock high time, 10 Mbps	t_8	SR	140	–	260	ns	
Clock low time, 10 Mbps	t_9	SR	140	–	260	ns	
Clock period, 100 Mbps	t_7	SR	40	–	–	ns	
Clock high time, 100 Mbps	t_8	SR	14	–	26	ns	
Clock low time, 100 Mbps	t_9	SR	14	–	26	ns	
Input setup time	t_{10}	SR	10	–	–	ns	
Input hold time	t_{11}	SR	10	–	–	ns	
Output valid time	t_{12}	CC	0	–	25	ns	

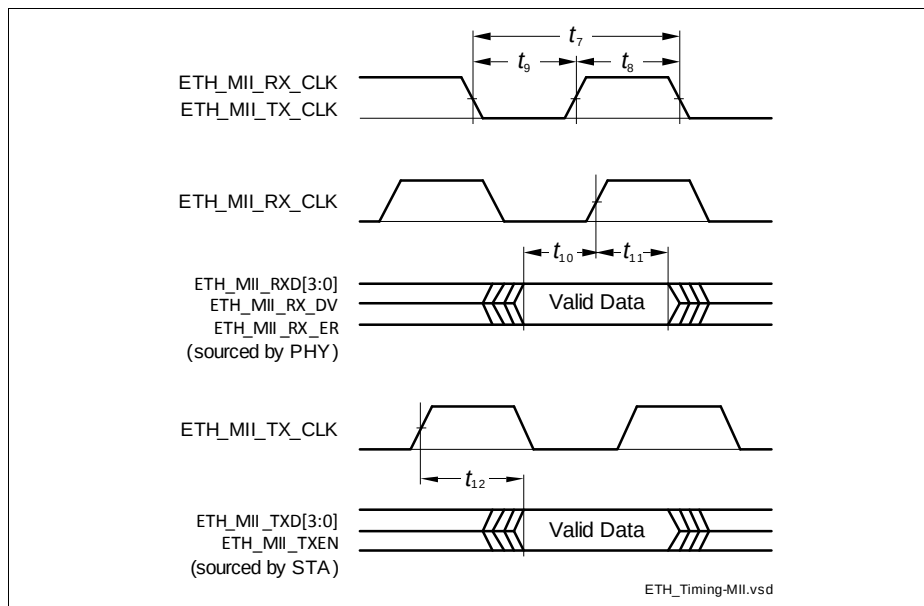


Figure 53 ETH MII Signal Timing

4.2 Package Outlines

Table 65 Differences PG-LQFP-14-18 to PG-LQFP-144-24

Change	PG-LQFP-144-18	PG-LQFP-144-24
Thermal Resistance Junction Ambient ($R_{\Theta JA}$)	22.4 K/W	21.0 K/W
Lead Width	0.22 ^{+0.05} mm	0.2 ^{+0.07} _{-0.03} mm
Lead Thickness	0.15 ^{+0.05} _{-0.06} mm	0.127 ^{+0.073} _{-0.037} mm
Exposed Die Pad outer dimensions	6.5 mm × 6.5 mm	6.5 mm × 6.5 mm
Exposed Die Pad U-Groove inner dimensions	n.a.	5.7 mm × 5.7 mm

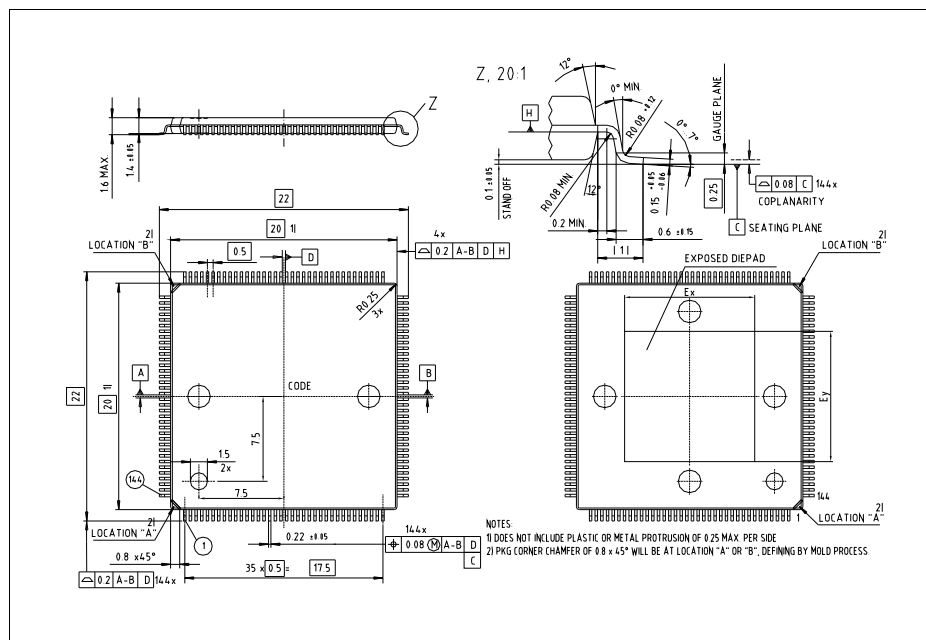


Figure 55 **PG-LQFP-144-18** (Plastic Green Low Profile Quad Flat Package)